



Attorney Docket No. 5649-919

PATENT

Grp 2814  
#4/A  
10/1/02  
Mullish

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re: Chung et al.  
Serial No.: 10/047,706 ✓  
Filed: Chung et al.  
For: SEMICONDUCTOR CAPACITORS HAVING  
TANTALUM OXIDE LAYER AND METHODS  
FOR MANUFACTURING SAME

Group Art Unit: 2814  
Confirmation No.: 3888

Date: March 14, 2002

Commissioner for Patents  
Washington, DC 20231

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TECHNOLOGY CENTER 2800

PRELIMINARY AMENDMENT

Dear Sirs:

Please enter the following Preliminary Amendment before examination of the present application. Pursuant to the rules for amendments under 37 C.F.R. §1.121, the specification has been amended herein using the replacement paragraphs format. The present amendment also includes a section entitled "**VERSION WITH MARKINGS TO SHOW CHANGES MADE**" attached hereto.

In the Specification:

Please replace the paragraph beginning at page 13, line 11, with the following rewritten paragraph:

A1

According to Si-woo Rhee et al., "Chemical Vapor Deposition Precursors for (Ba, Sr)TiO<sub>3</sub> Films", 6<sup>th</sup> Korean Semiconductor Seminar, the deposition of Ti may be carried out using the surface reaction as a rate determining step, and high coverage may be achieved by virtue of the surface movement of Ti.

REMARKS

Applicants have amended the specification to correct a minor typographical error. This amendment presents no new matter, and Applicants respectfully request entry.